

On-Chip Quantum Optics using Electrically Driven Quantum Dot - Micropillar Cavities

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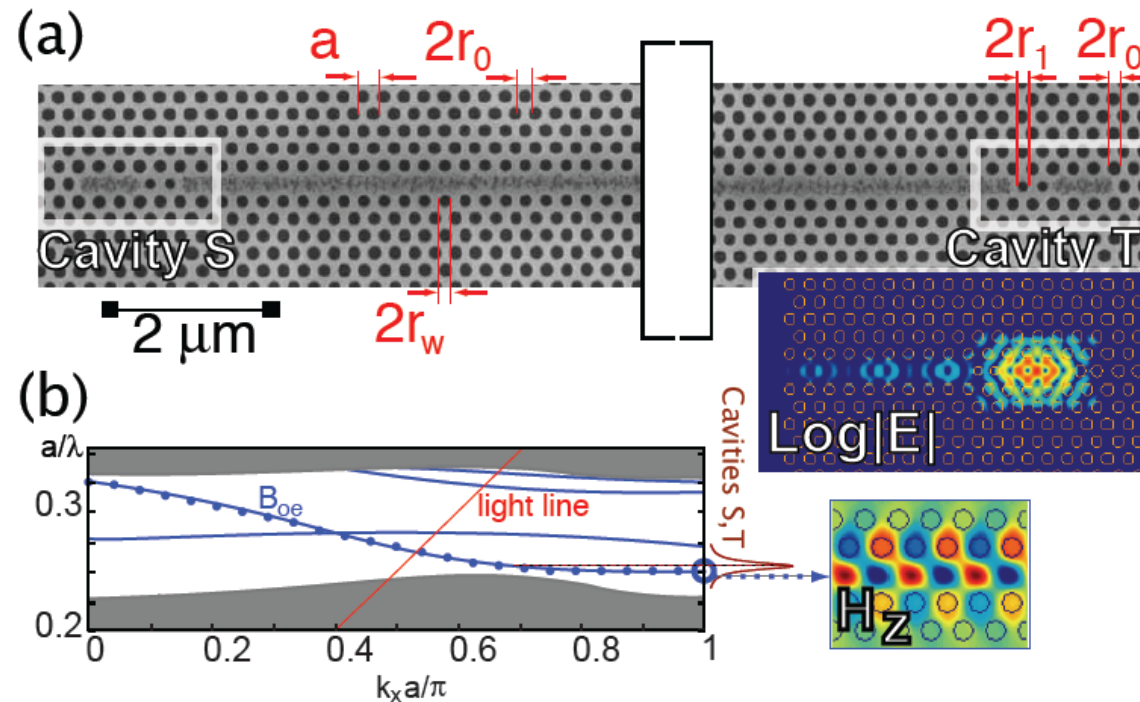
BMBF via „QPENS“, BMBF „QuaHL-rep“,

EU via „TREASURE“

Motivation

- On-chip photonic networks: central topic in modern nanotechnology
- Goal: On-chip integration of linear elements, non-linear elements, detectors, light sources ...

On-chip transfer of single photons in photonic crystals

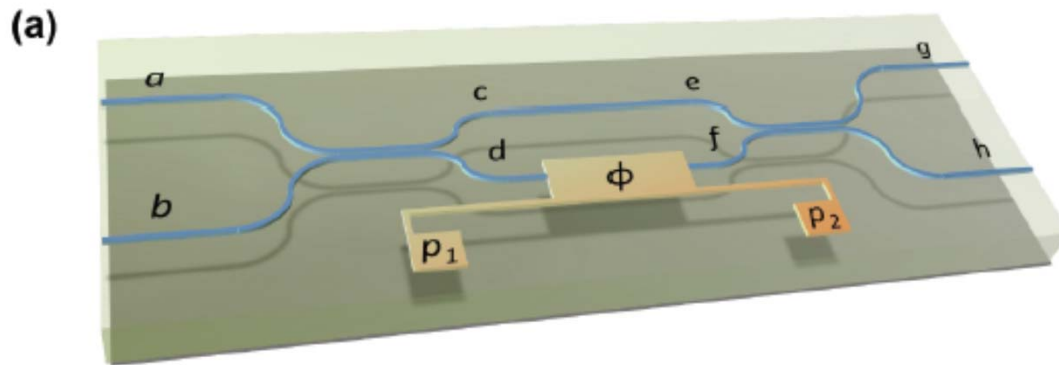


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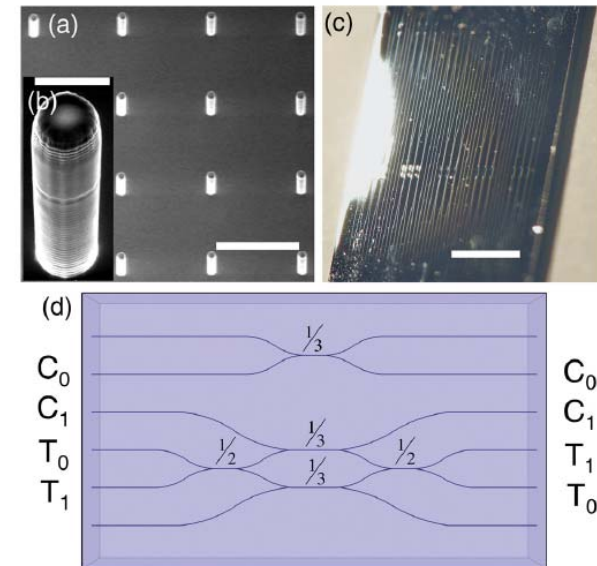
Implementation of quantum operations using coupled waveguides

Multi-photon entanglement



J. C. F. Matthews et al., Nat. Phot. 3, 346 (2009)

CNOT gate

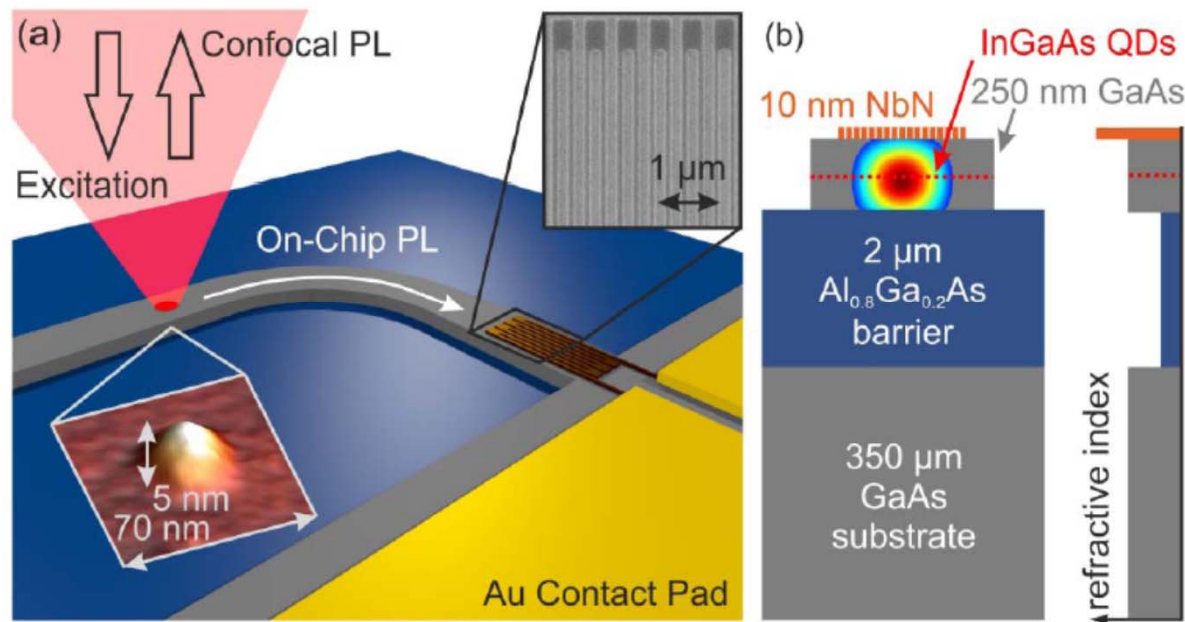


M. A. Pooley et al, APL 100, 211103 (2012)

Motivation

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Monolithically integrated photon detector



G. Reithmaier et al., Scientific Reports 3, 1901 (2013), see **ThOM3**

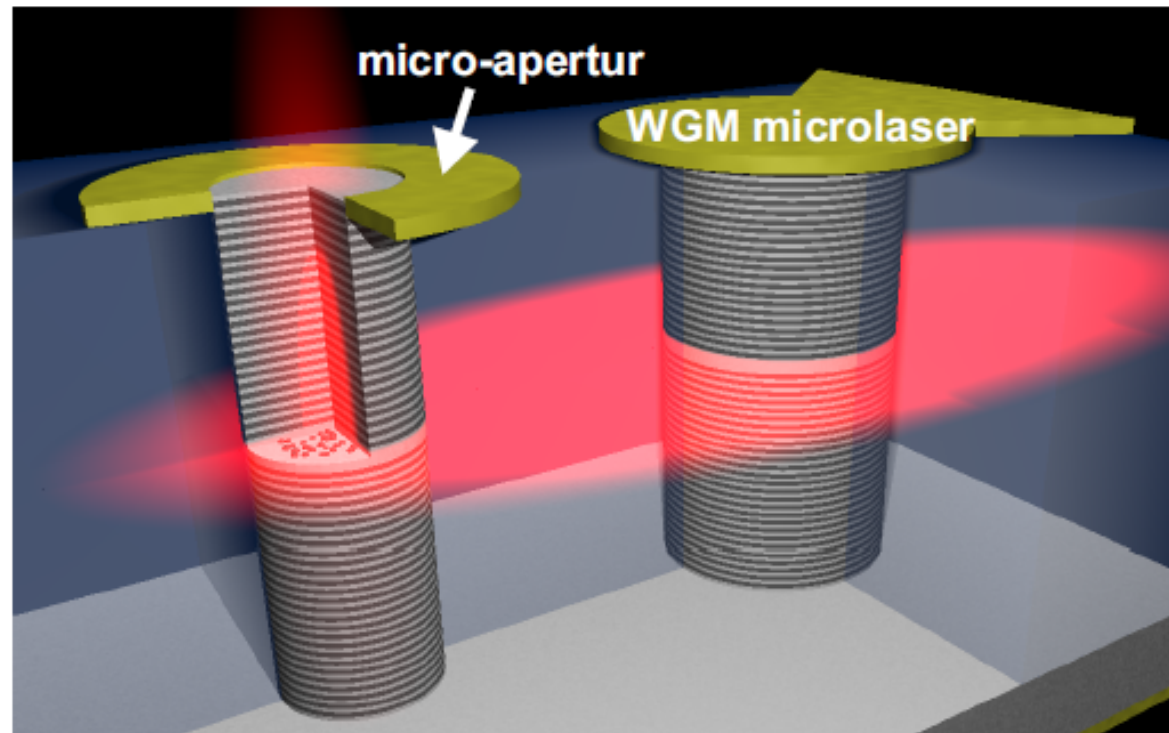
Motivation

- On-chip photonic networks: central topic in modern nanotechnology
- Goal: On-chip integration of linear elements, non-linear elements, detectors, light sources ...
- So far: lack of suitable monolithically integrated, electrically driven light sources

Our approach:

On-chip quantum optics experiments and non-classical light sources using integrated electrically driven micropillar lasers for resonant excitation of coupled QD - microcavities

On-Chip Quantum Optics Approach Using Micropillar Cavities

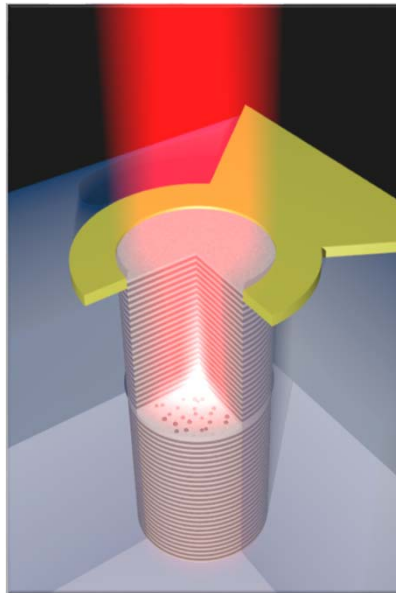


Outline

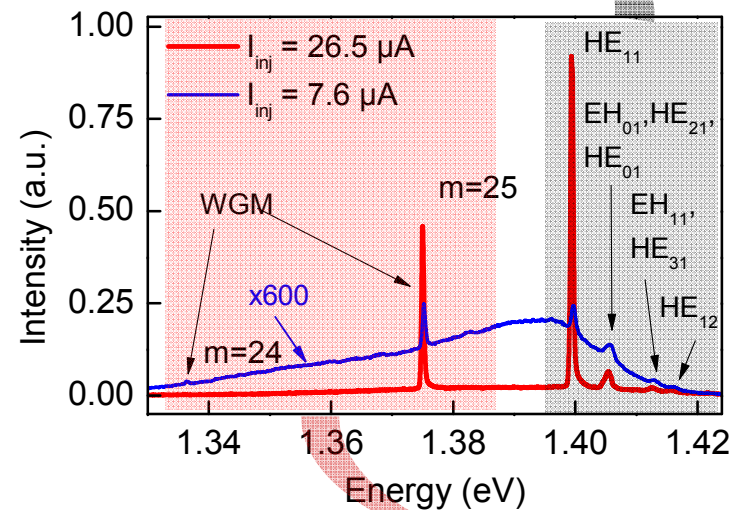
- Motivation
- Introduction & Technology
- On-chip quantum optic experiments using an integrated WGM laser
- Directional lateral emission from Limaçon microlasers
- Deterministic in-situ electron-beam lithography
- Outlook & Summary

Vertical & Lateral Emission from QD – Micropillar Cavities

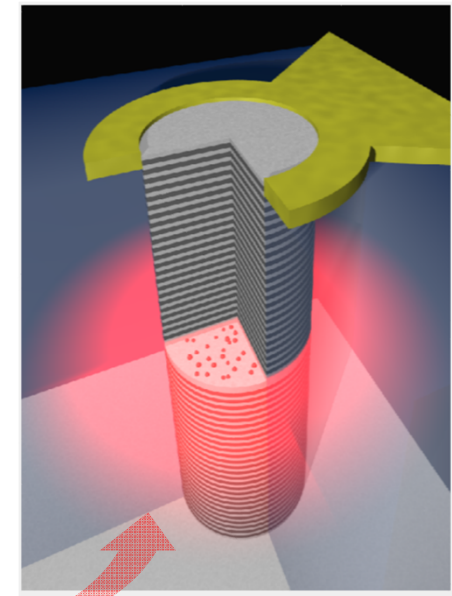
Vertical (HE_{11} , ...) – emission from micropillar lasers



Co-existence of HE_{11} - and WGM-Lasing:



Lateral WGM – emission from micropillar lasers



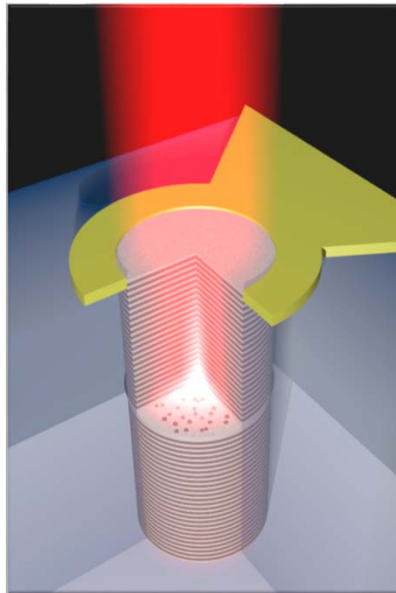
Low-threshold (few μA), high- β (~ 0.1) via HE_{11} AND WGM modes!

S. Reitzenstein et al., APL 93, 061104 (2008)
Efficient SPS: T. Heindel et al., APL 96, 011107 (2010)

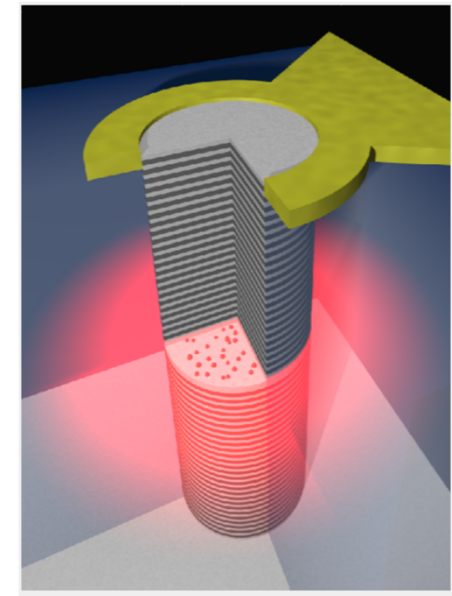
F. Albert et al., APL 97, 101108 (2010)

Vertical & Lateral Emission from QD – Micropillar Cavities

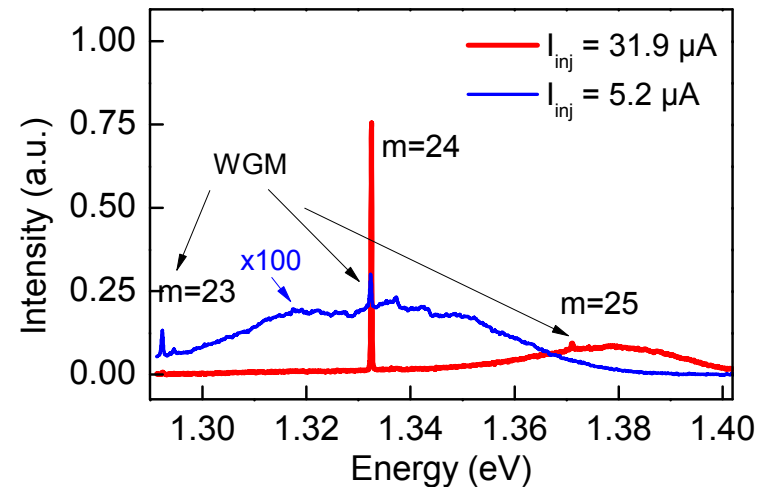
Vertical (HE_{11} , ...) – emission from micropillar lasers



Lateral WGM – emission from micropillar lasers



Pure WGM-Lasing:

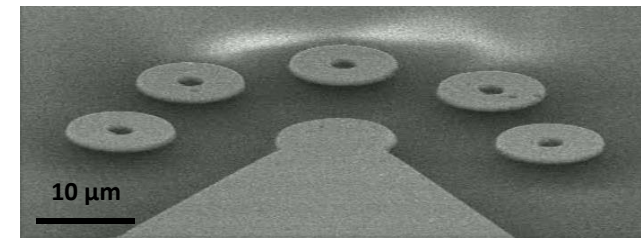
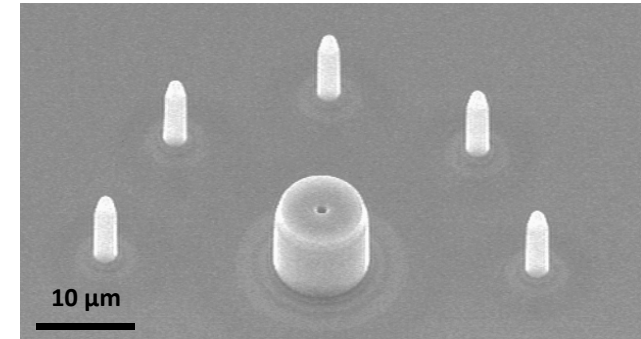
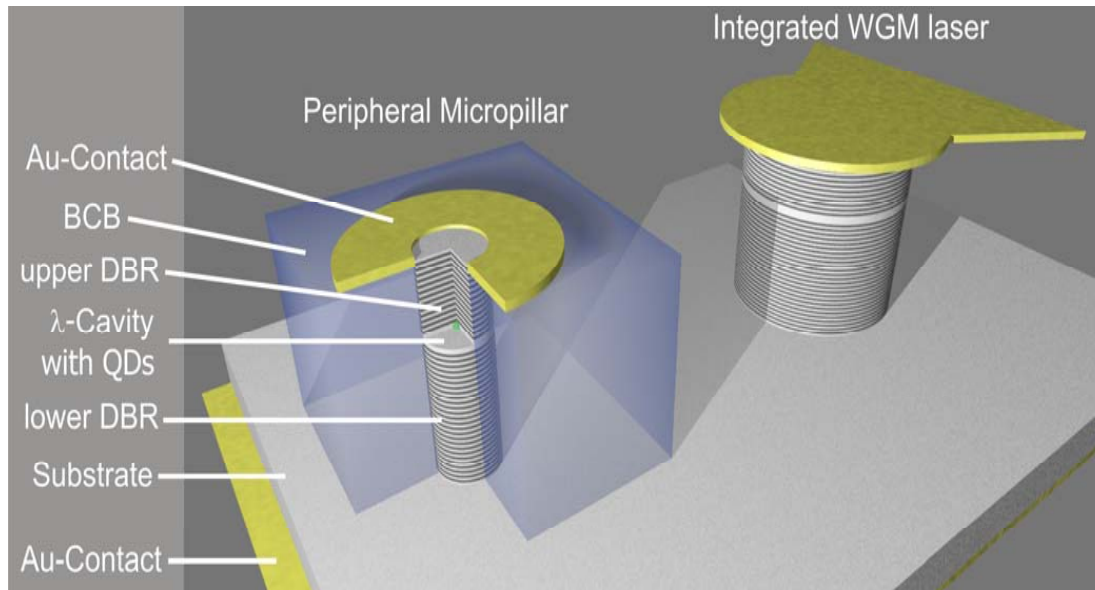


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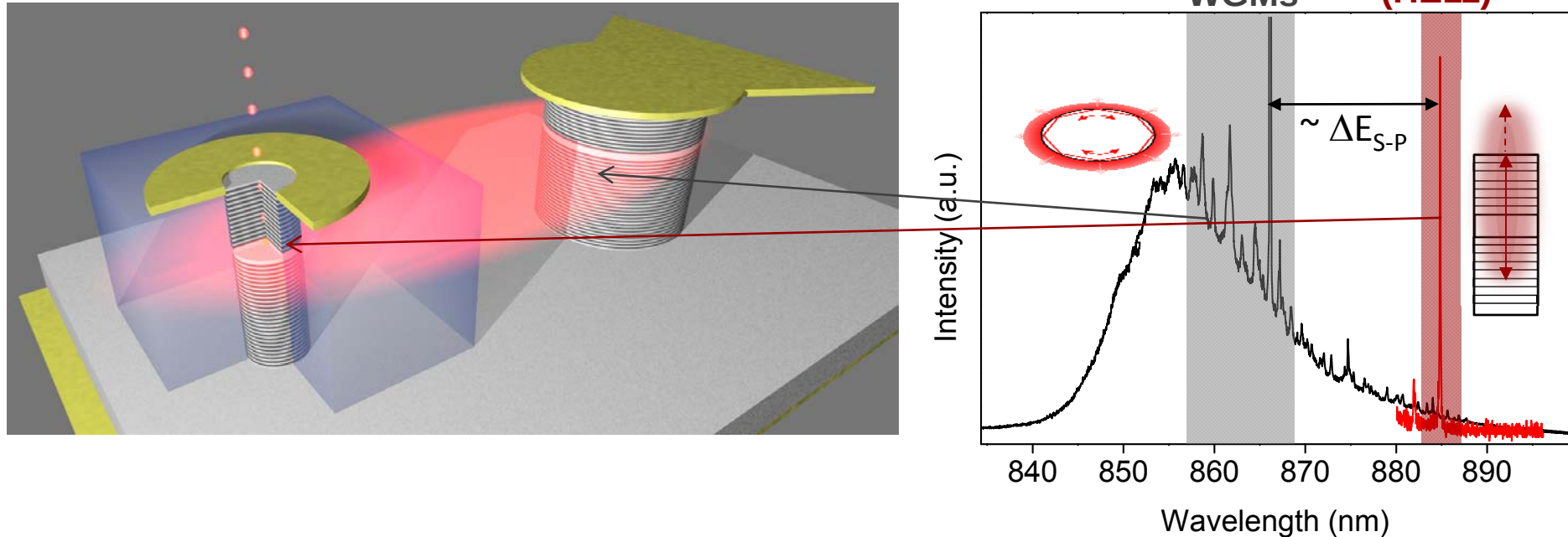
F. Albert et al., APL 97, 101108 (2010)

Sample Fabrication



- High-Q, doped planar AlAs/GaAs-microcavity structure
- Single layer of self-assembled InGaAs QDs
- Electrically driven WGM microlaser at the center (6.0 μm diameter)
- In-plane excitation of five peripheral “target” micropillar cavities (1.6 - 2.5 μm diameter)

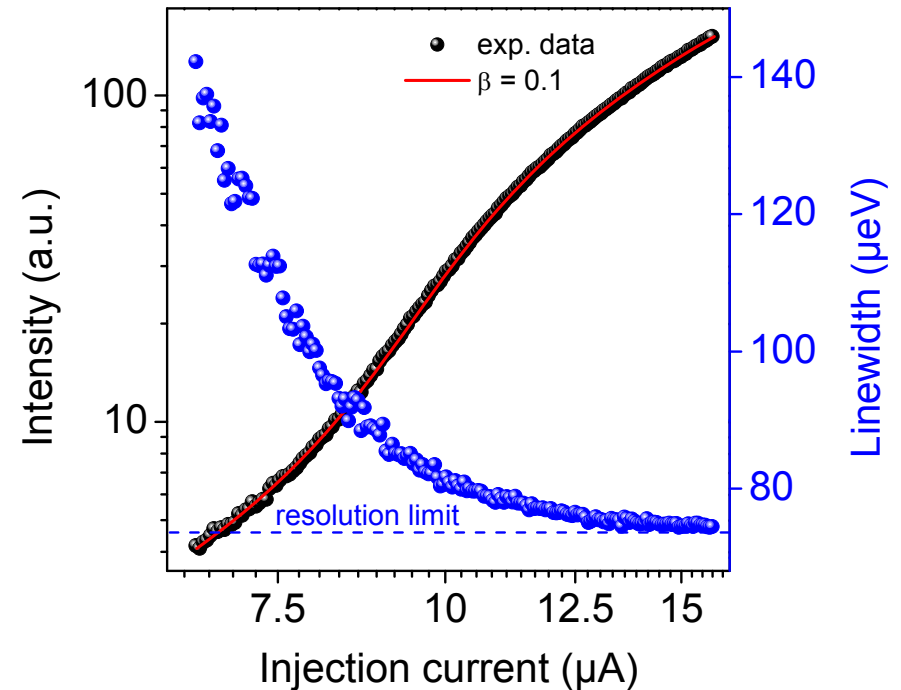
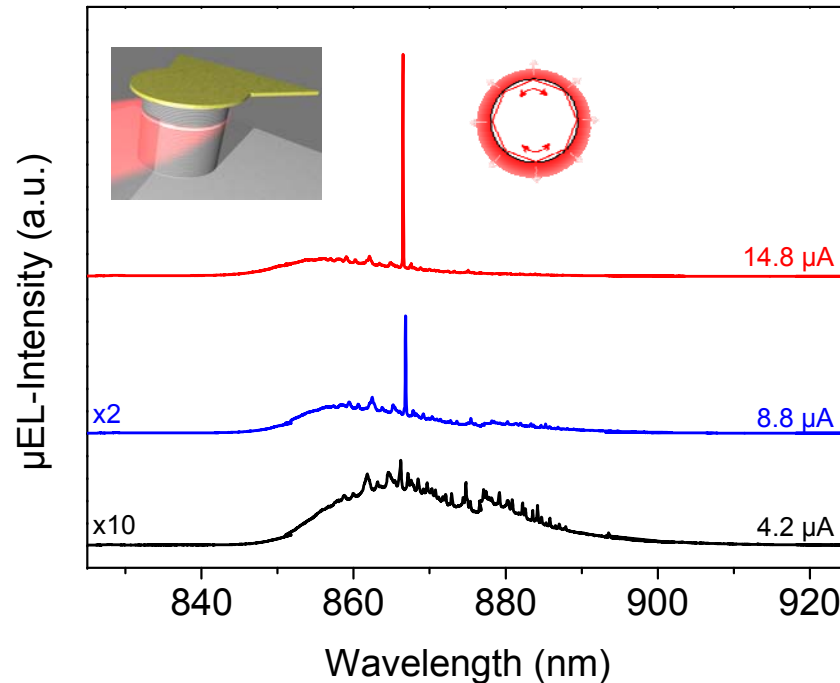
Optical Mode Design & QD Gain Characteristics



Technological Challenges:

- Design planar microcavity and active QD medium to provide sufficient gain for WGM lasing AND the possibility of single-QD cQED experiments
- Ensure that WGM microlaser emits at p-shell energy of single QDs (p-shell excitation: beneficial for the generation of indistinguishable photons)
- State-of-the-art processing with very high yield

Integrated Electrically Driven WGM-Microlaser

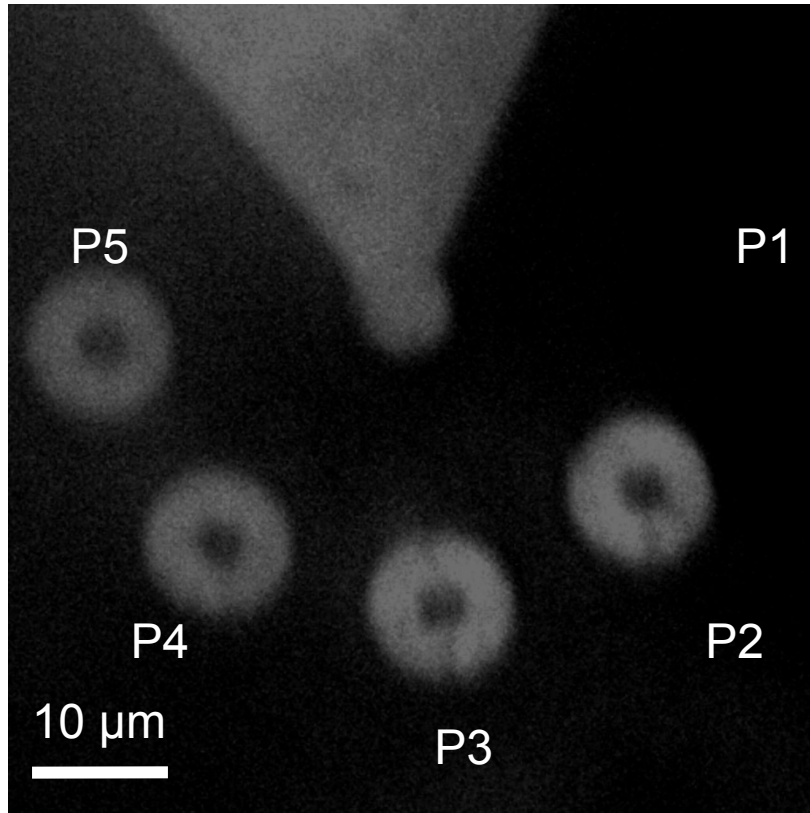


Electrically pumped central micropillar ($T = 15\text{K}$):

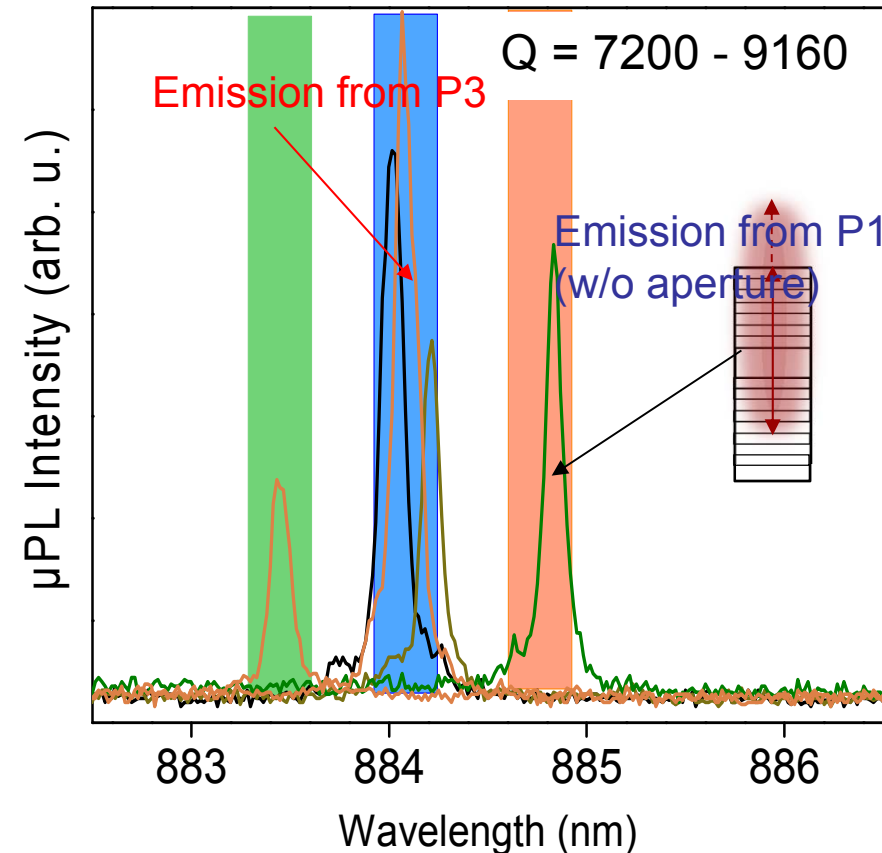
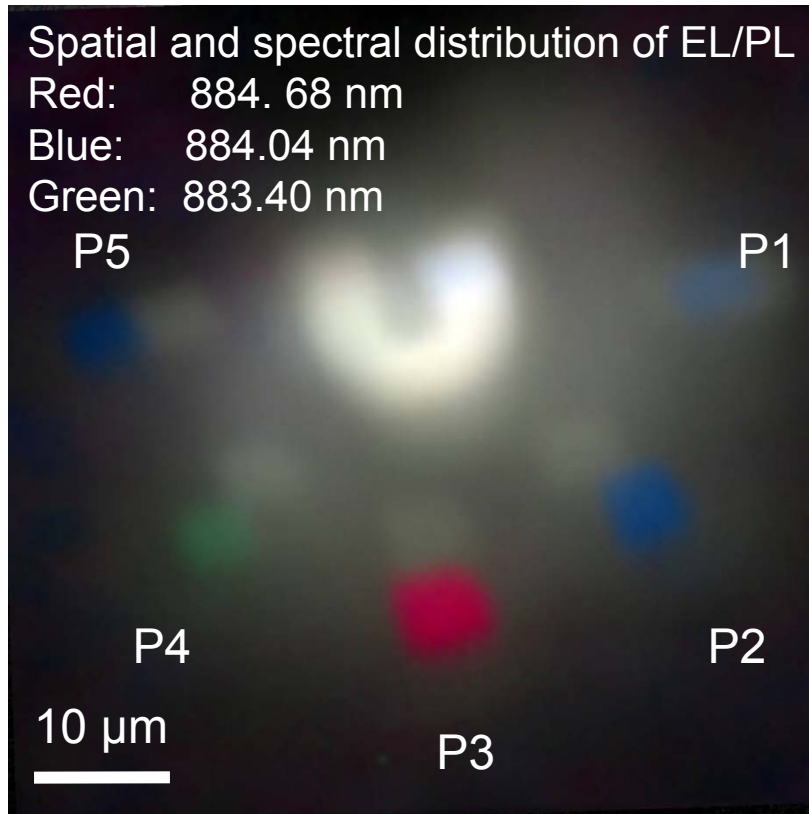
- μEL features WGM-lasing with ultralow threshold current of $I_{\text{th}} \approx 8 \mu\text{A}$ and $\beta = 0.1$
- Single mode WGM lasing at $\lambda = 866.5 \text{ nm}$

Central micropillar:
High- β WGM microlaser acts as low-threshold on-chip microlaser

In-plane Excitation of Peripheral Micropillars



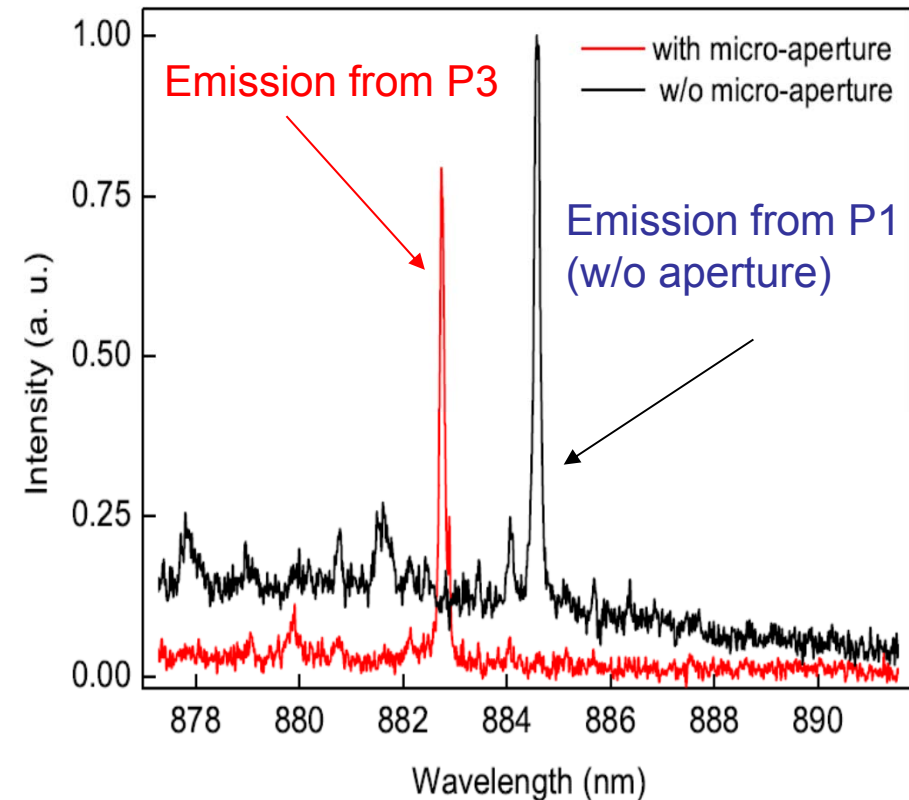
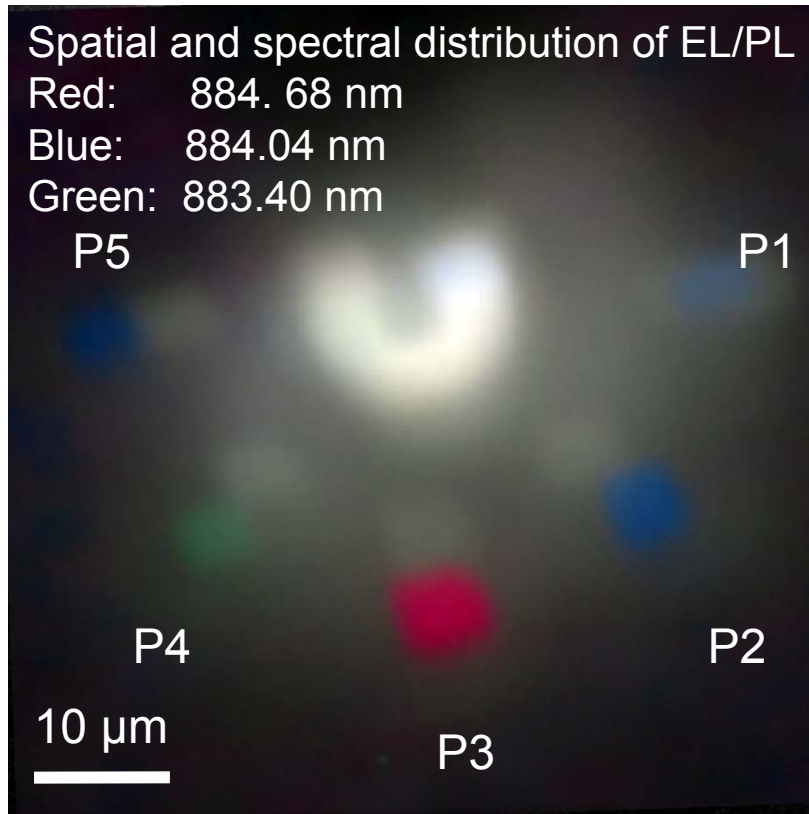
In-plane Excitation of Peripheral Micropillars



Peripheral micropillars ($d_c = 2.5 \mu\text{m}$):

- μPL of peripheral micropillars under WGM-microlaser excitation @ 867 nm
- Absorption limited Q-factors close to 10.000

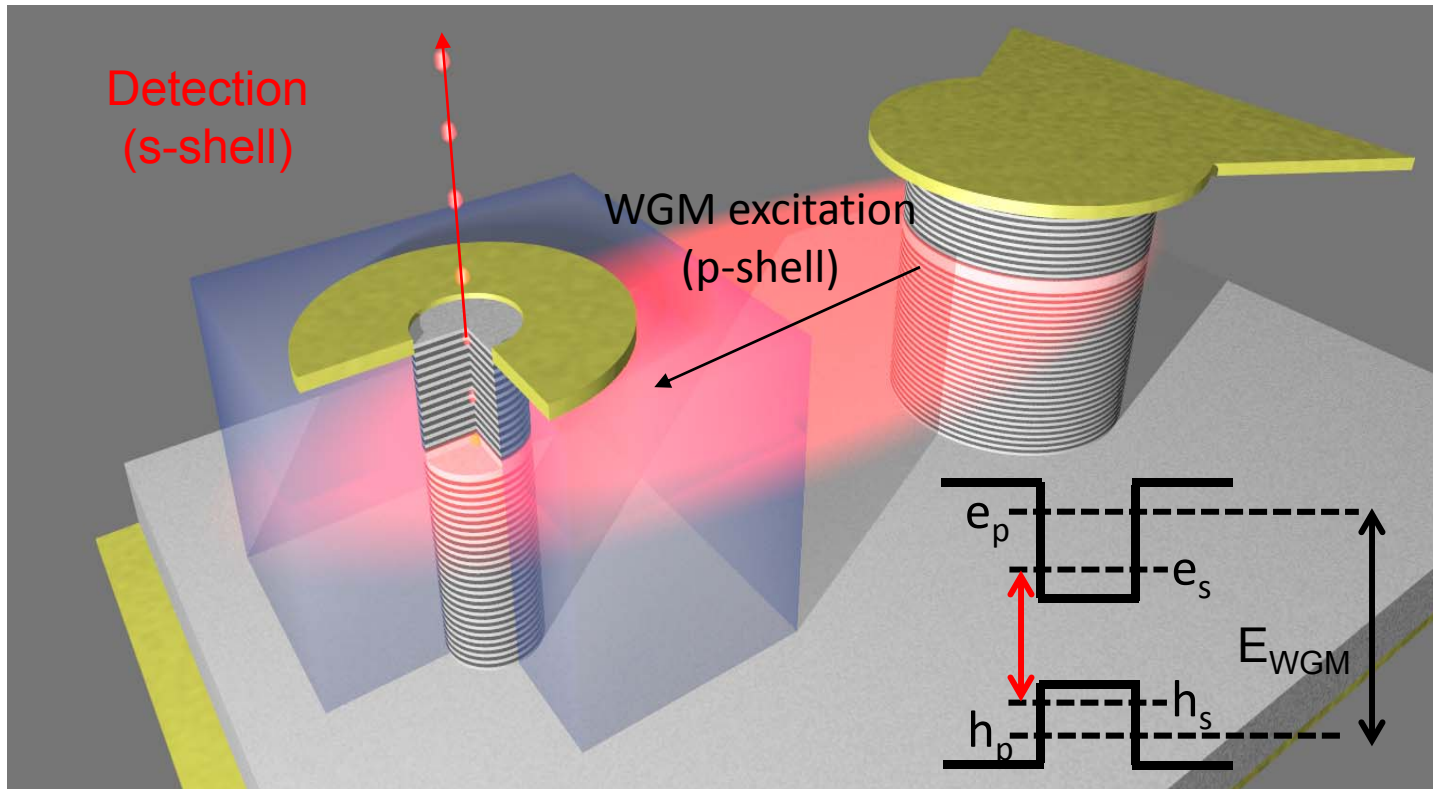
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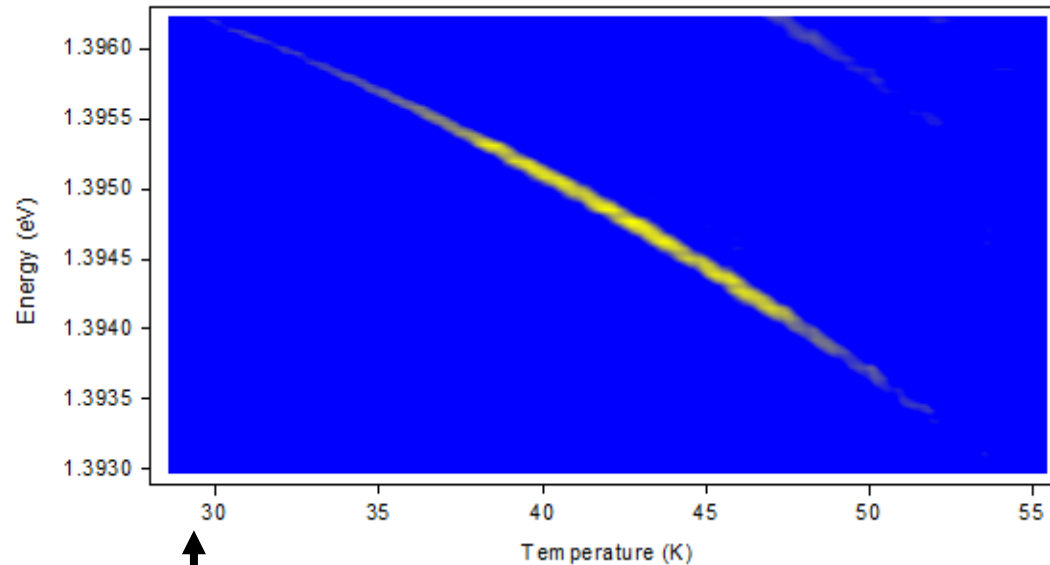
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- Absorption limited Q-factors close to 10.000
- Supression of stray light from WGM laser by microaperture

Resonant Excitation – On-Chip μ PLE

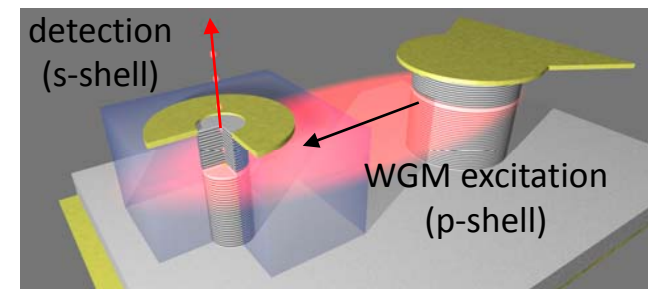
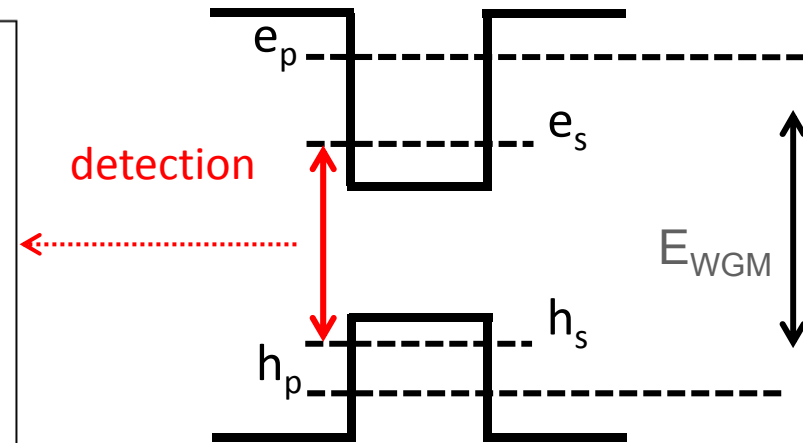


Resonant Excitation – On-Chip μ PLE



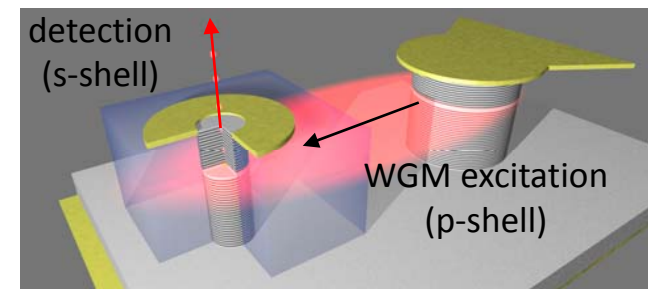
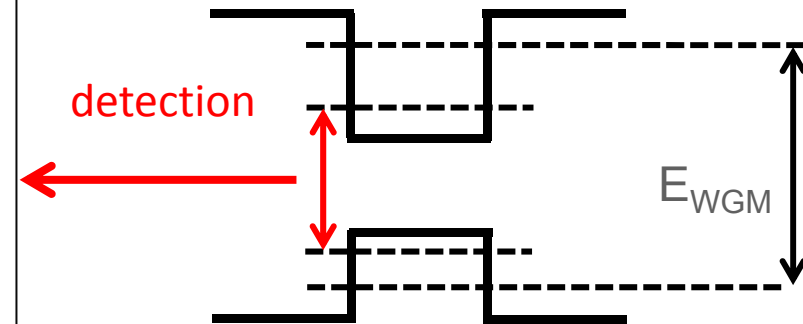
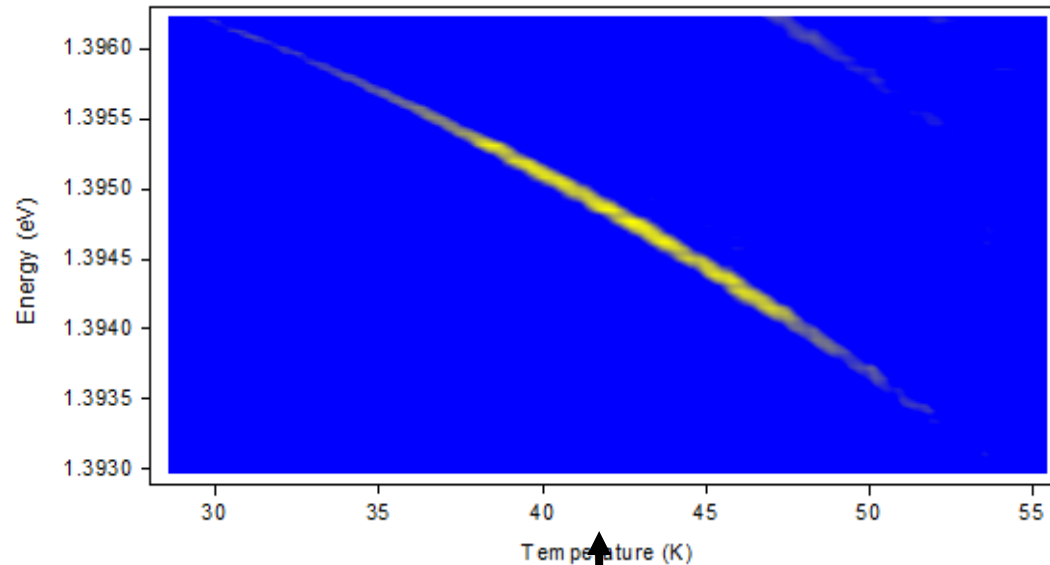
μ PL of peripheral micropillar:

- Excitation by fixed WGM mode at $E_{\text{WGM}} = 1.426$ eV
- Temperature variation $\rightarrow$ resonant s-shell emission when $E_{\text{p-shell}} = E_{\text{WGM}}$



$\Rightarrow$ Resonant excitation of QD when WGM laser-mode hits p-shell of QD in micropillar at $T_{\text{res}} \approx (40 - 45)$ K (s-p-splitting: ≈ 20 nm, 31 meV)

Resonant Excitation – On-Chip μ PLE

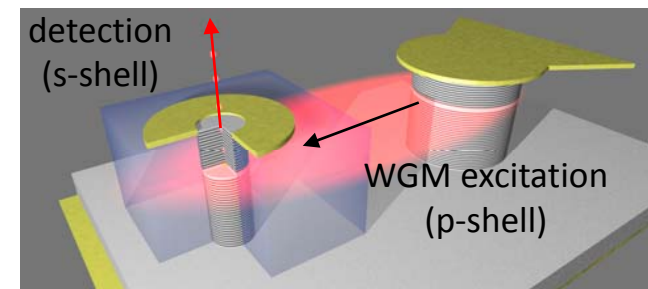
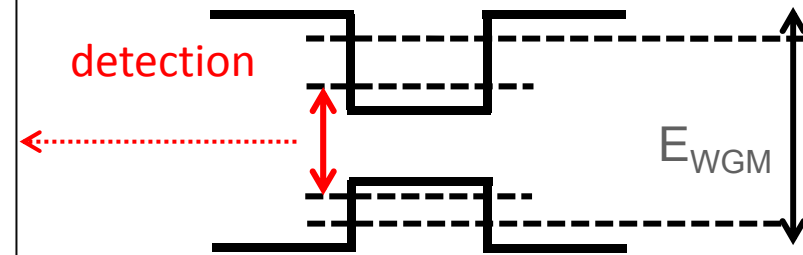
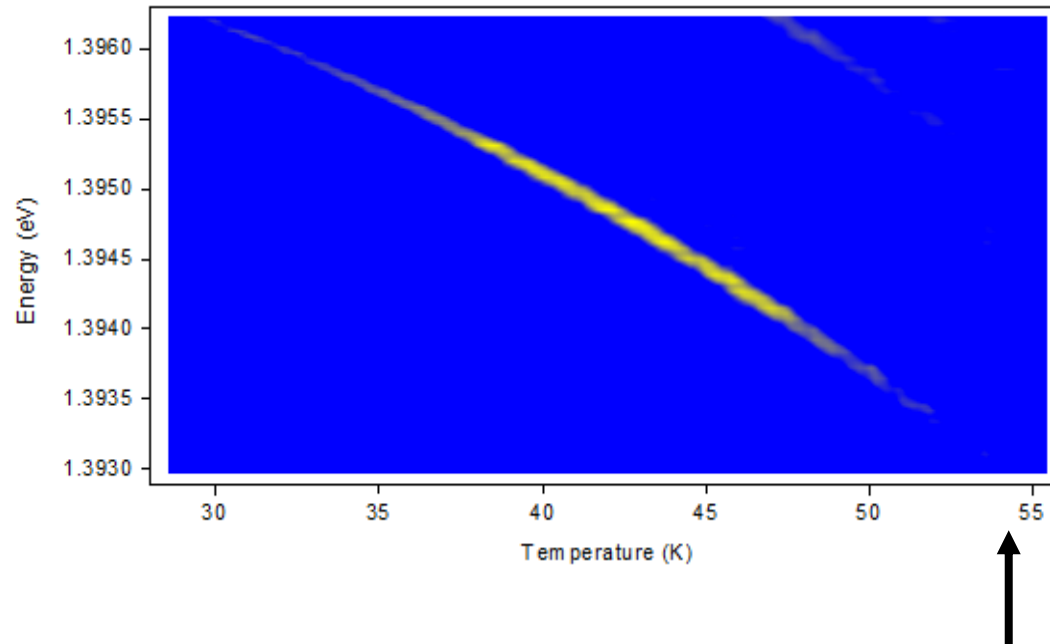


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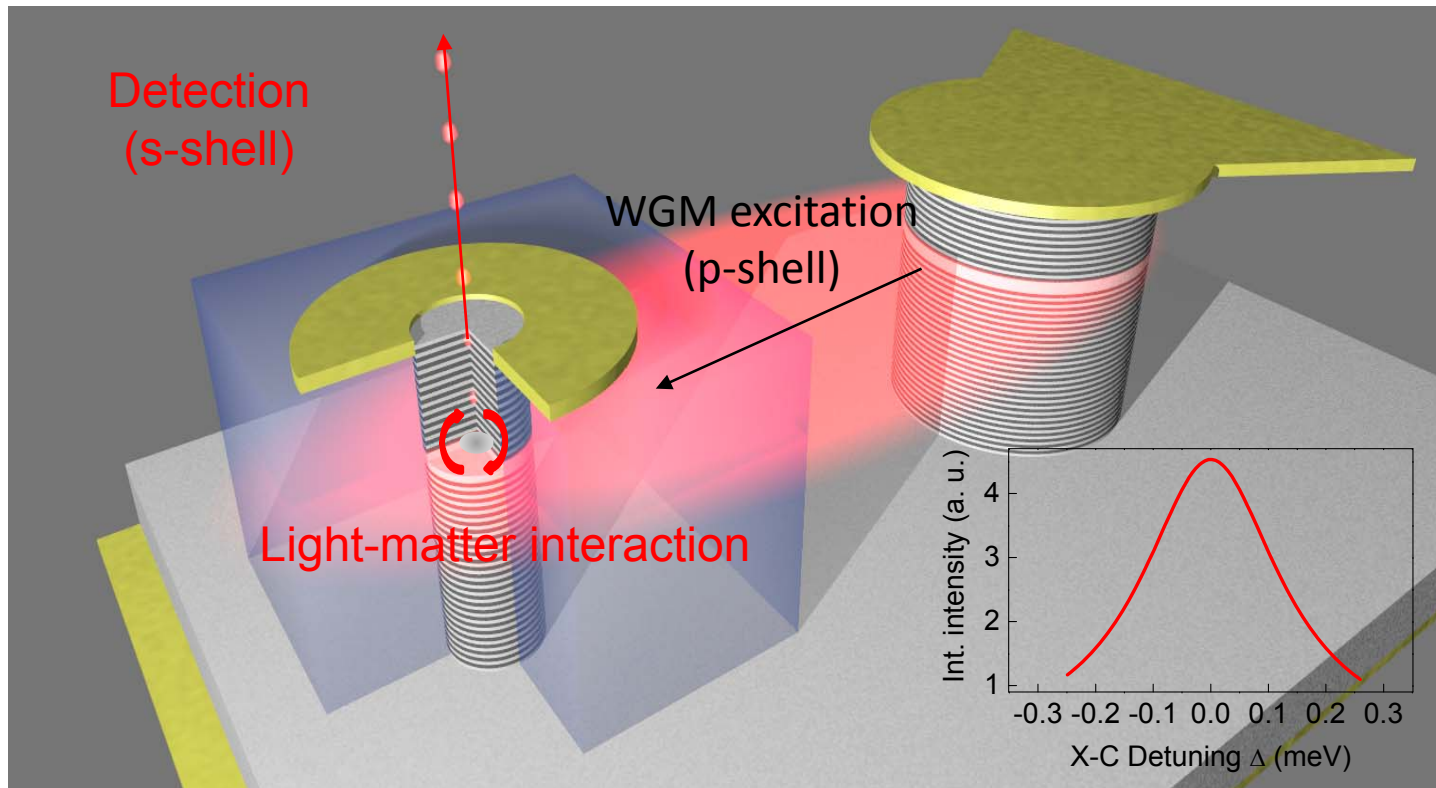


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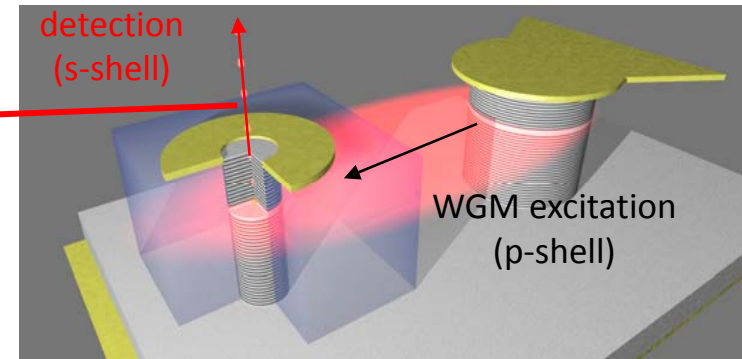
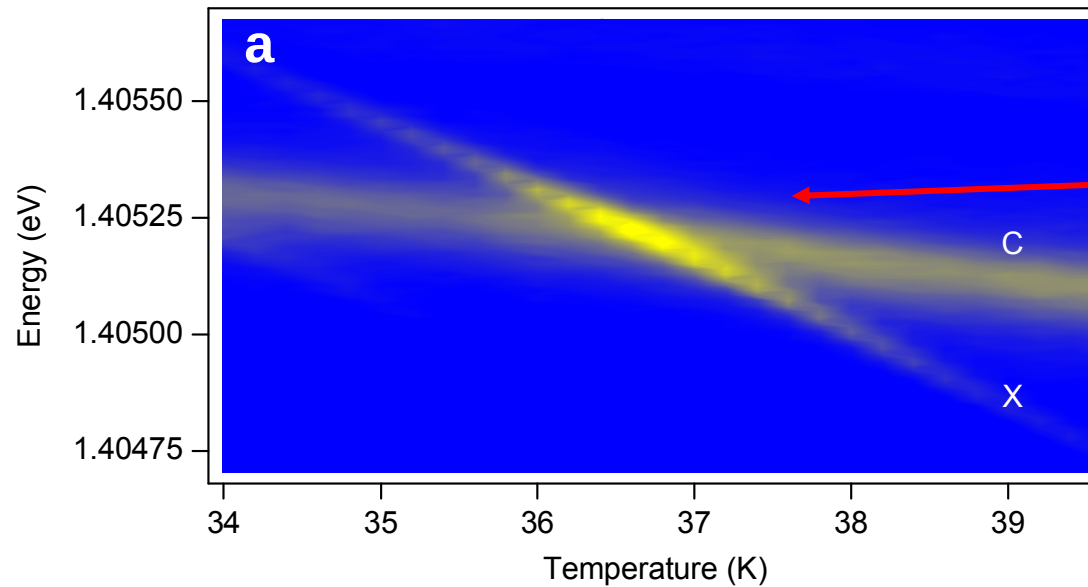
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On-chip cQED - Weak Coupling Regime

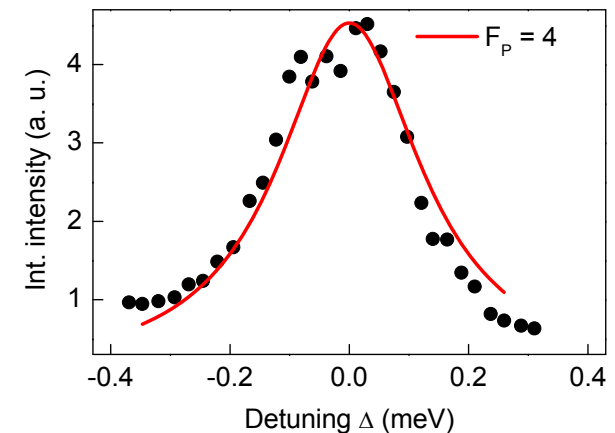


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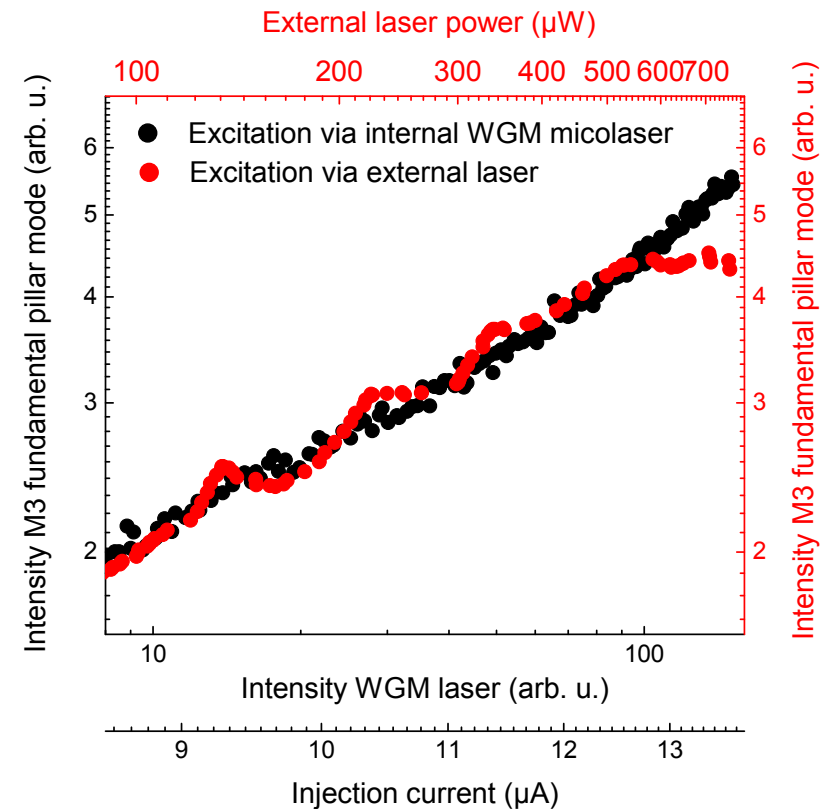
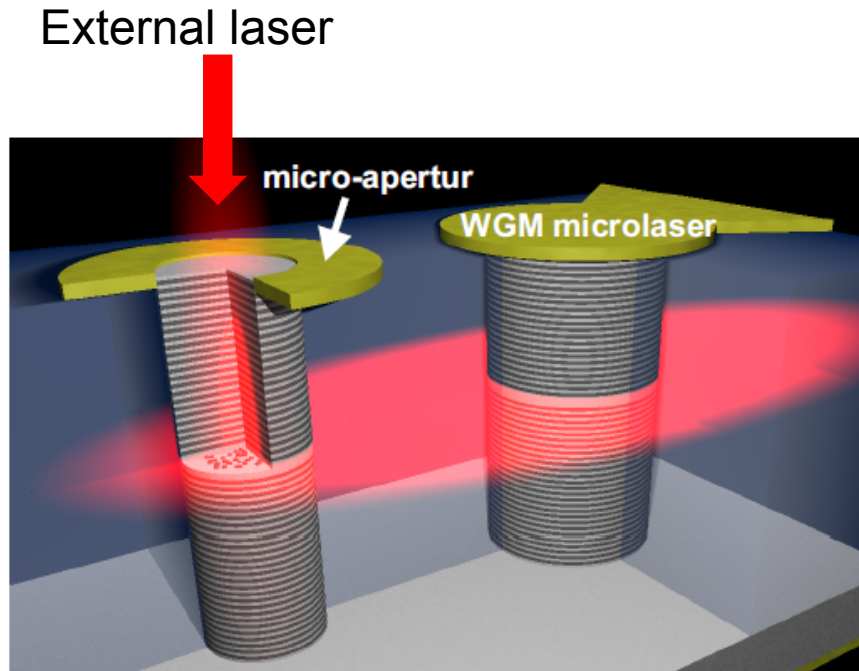


El. pumping of micropillar by WGM laser-mode at 1.431 eV

- ⇒ In-plane p-resonant excitation of QD in micropillar
- ⇒ Strong enhancement of X-emission at $T_{\text{res}} = 36.5$ K
- ⇒ Purcell factor: $F_p = 4$



About Excitation Efficiency

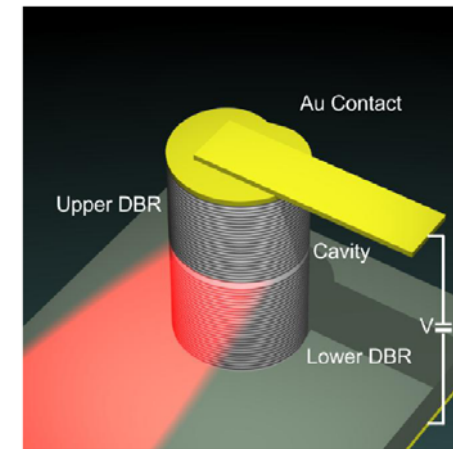
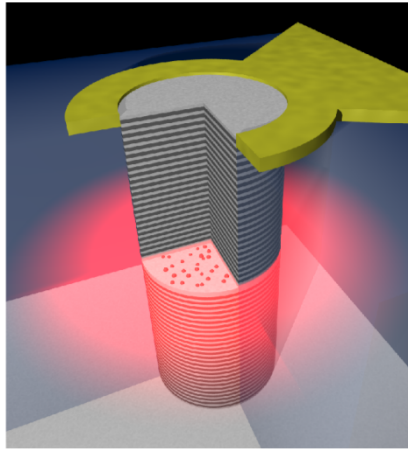


Comparison: Excitation of peripheral micropillar

via external laser vs. internal WGM microlaser, both at 867 nm

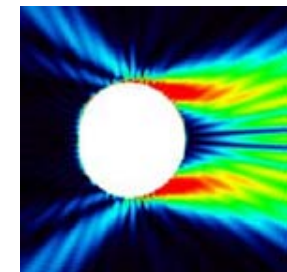
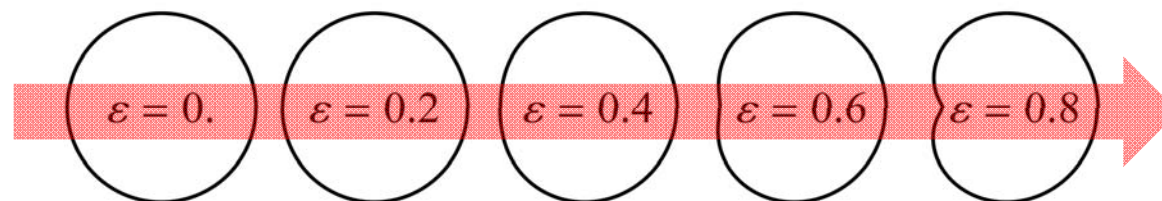
External powers between 100 and 700 μW $\leftrightarrow$ injection currents between 9 – 13 μA

A Way to Enhance Excitation Efficiency: Directional Lateral WGM Lasing via Limaçon Cross-Section

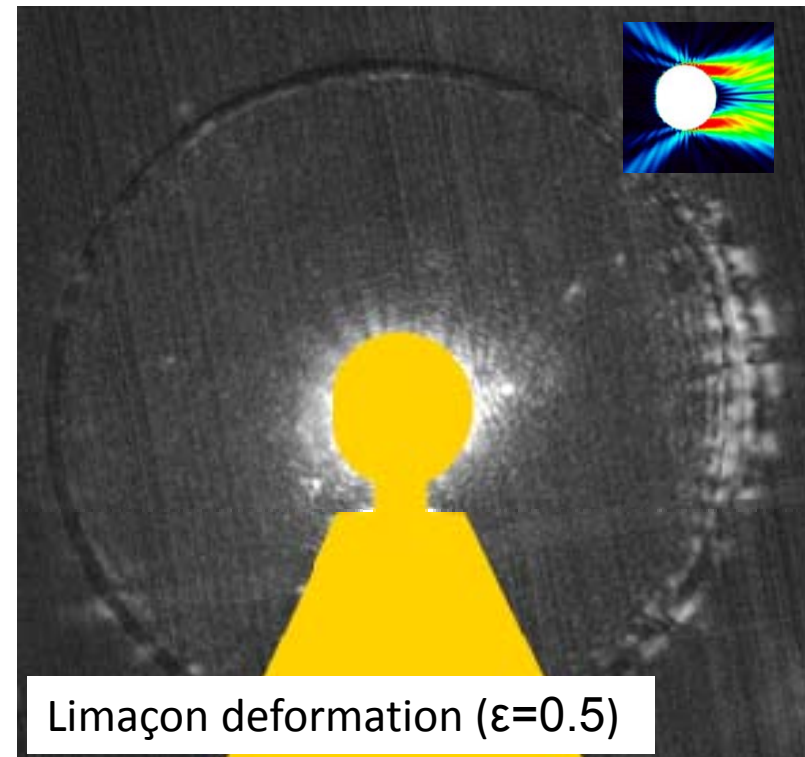
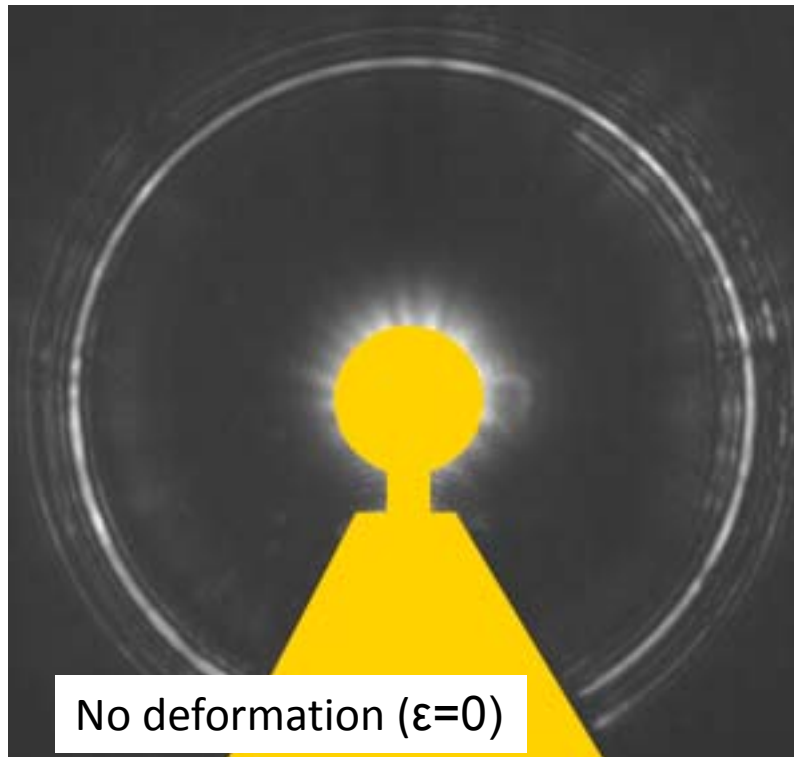


Enhancement of coupling efficiency via directional in-plane emission
→ Deterministic deformation of micropillar cross-section by Limaçon shape:

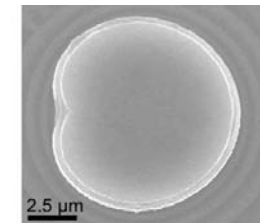
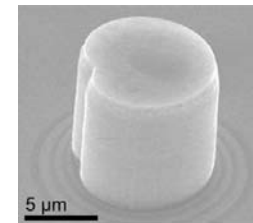
$$R(\theta) = R_0(1 + \varepsilon \cos\theta)$$



Directional emission from WGM microlasers

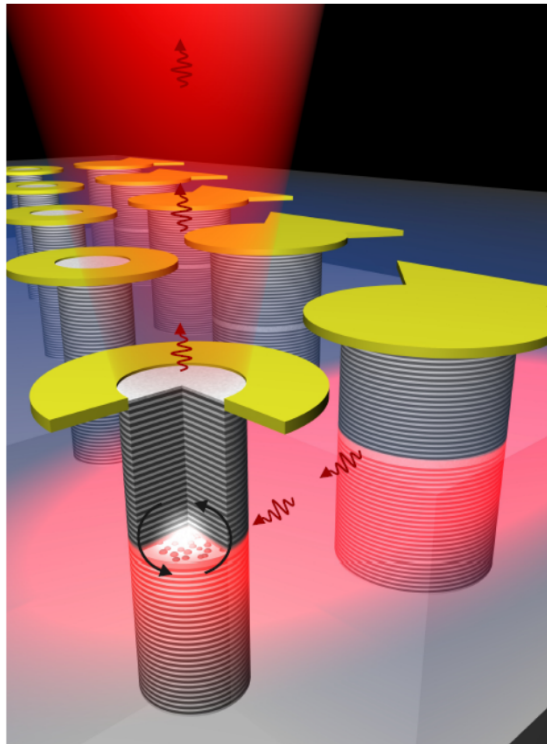


Limaçon deformation ($\epsilon \approx 0.5$) clearly leads to directional in-plane emission!

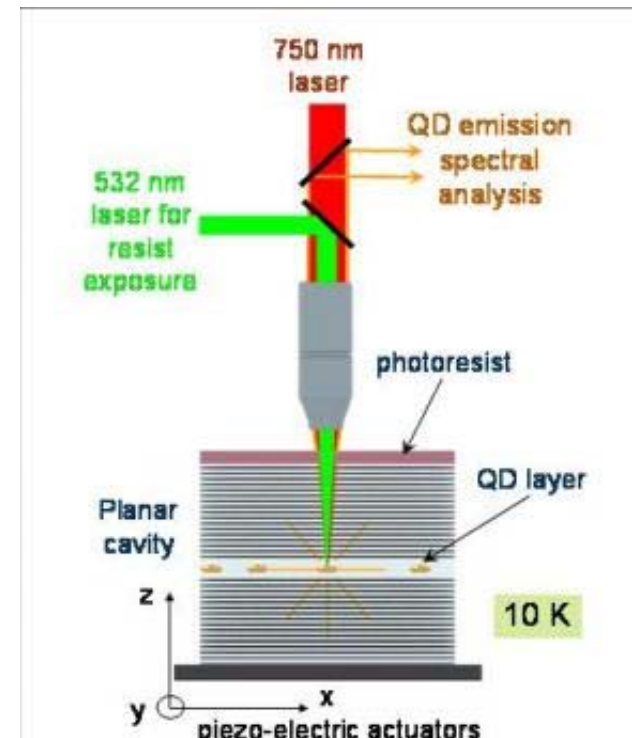


Outlook – Deterministic Fabrication Technology

Arrays of quantum light sources
req. spectral and spatial QD-cavity matching



In-situ optical lithography,
A. Dousse et al., PRL 2008

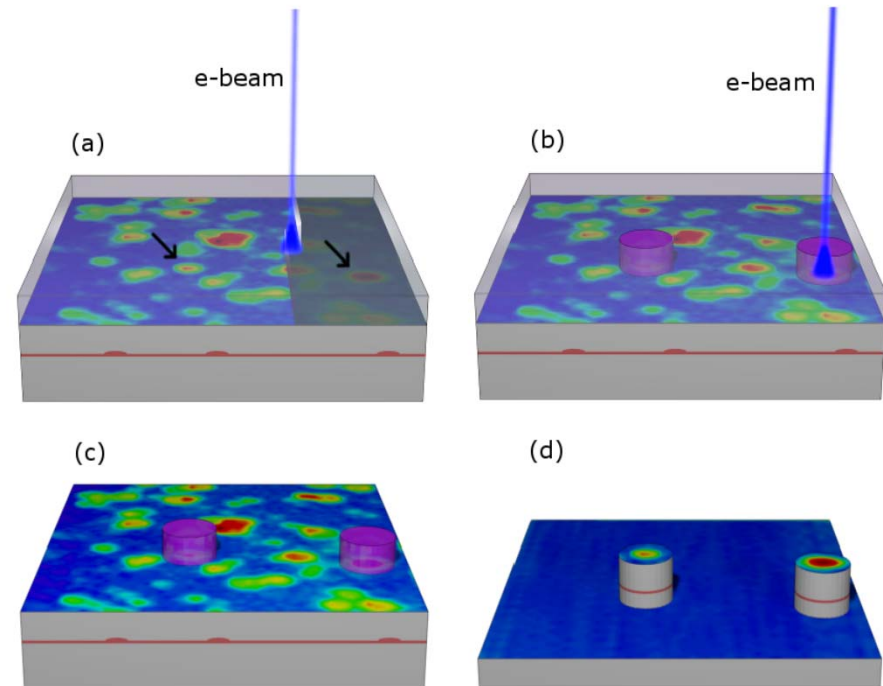
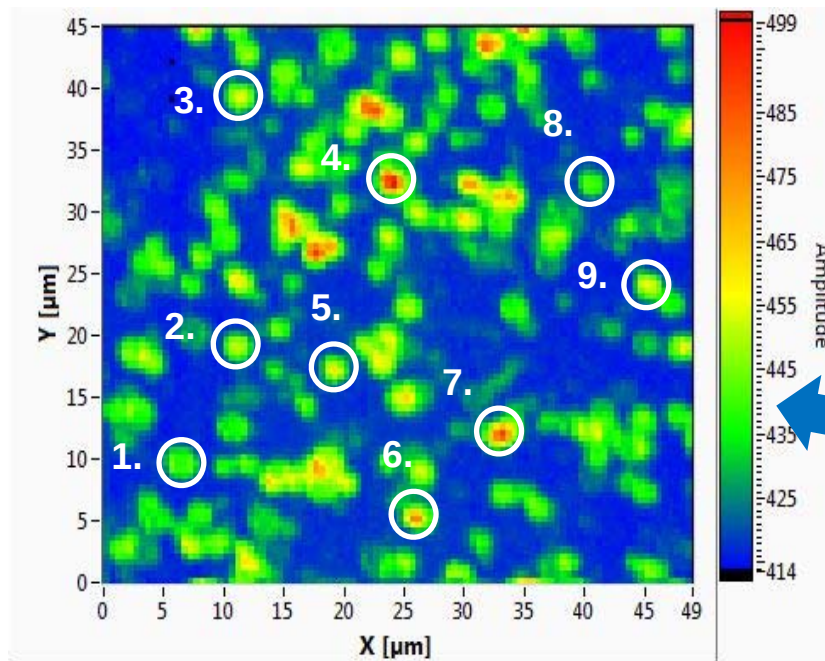


Alternative concept:
Deterministic high-resolution electron beam lithography using low temperature
cathodoluminescence

Cf.: In-situ nanowire lithography, F. Donatini & Le Si Dang, Nanotechnology 2010

In-situ, High-Resolution Cathodoluminescence-Lithography

CL-map during CL-lithography

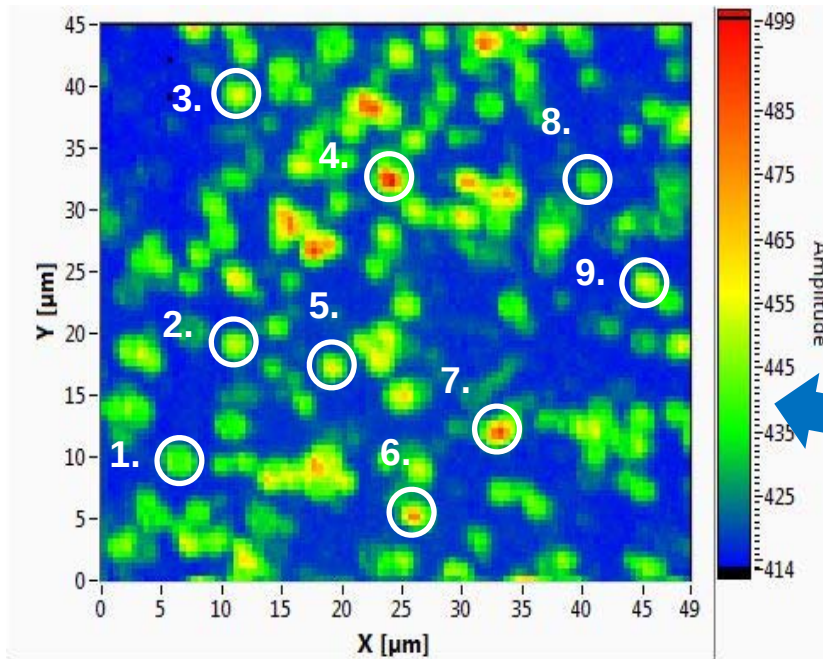


Deterministic fabrication of single QD – structures:

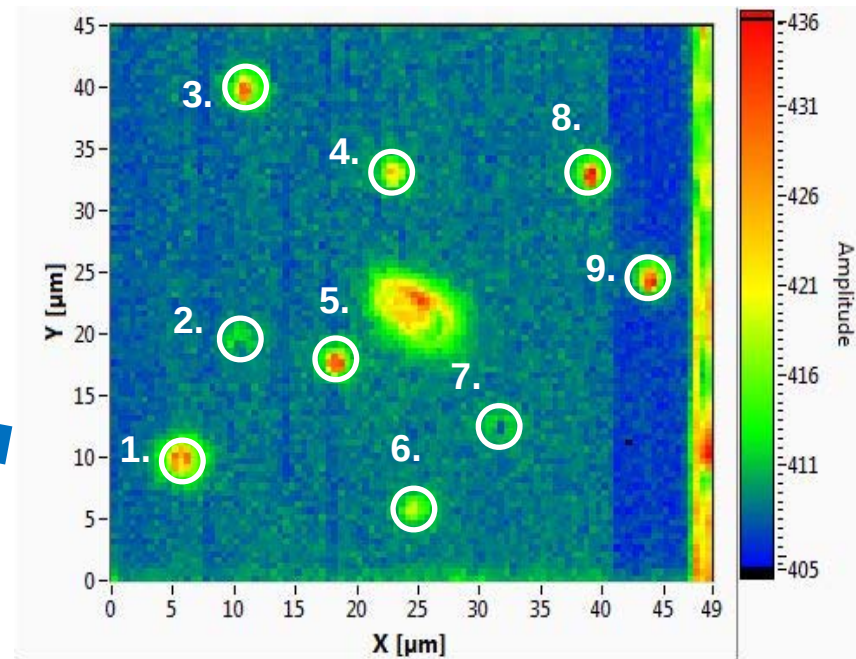
- CL-scanning of InGaAs-QD sample to identify suitable QDs (a)
- In-situ e-beam writing of mesas with < 500 nm diameter (b)
- Development (c)
- CL and μ PL to characterize single-QD mesas $\rightarrow$ linewidths < 10 μ eV, $g^{(2)}(0) < 0.05$

In-situ, High-Resolution Cathodoluminescence-Lithography

CL-map during CL-lithography



CL-map after CL-lithography

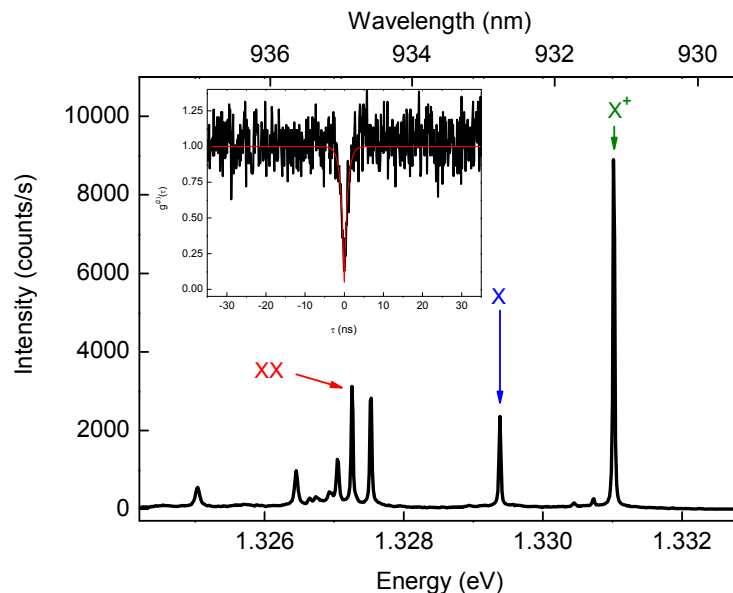


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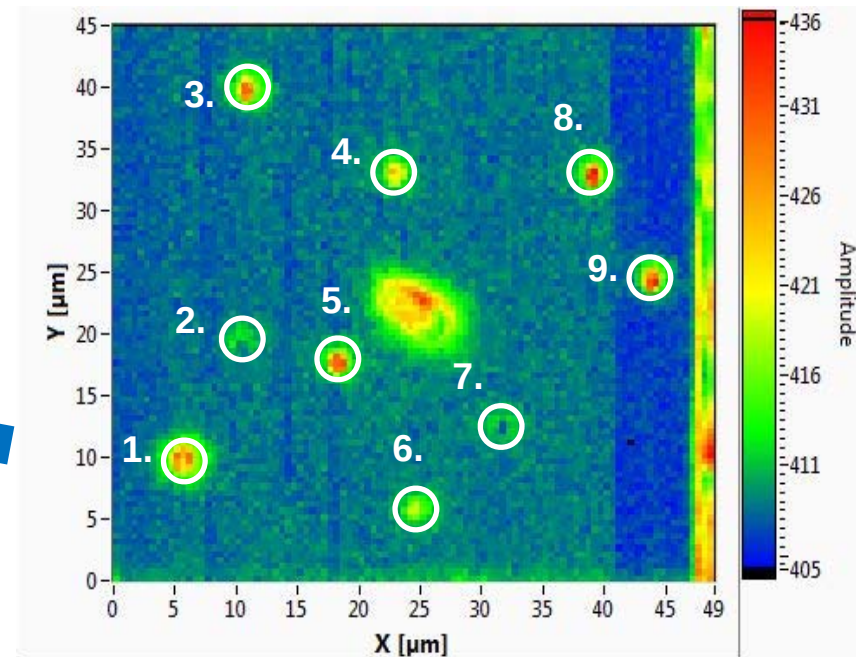
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In-situ, High-Resolution Cathodoluminescence-Lithography

μ PL-spectrum after CL-lithography



CL-map after CL-lithography



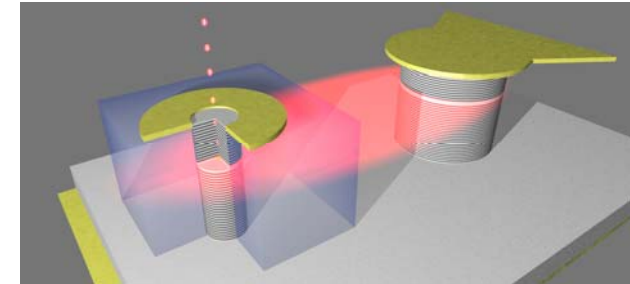
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Summary

On-chip quantum optic experiments using integrated WGM lasers:

- Electrically driven WGM microlaser acting as on-chip light source
- In-plane resonant p-shell excitation
- On-chip cQED experiment in the weak coupling regime featuring $F_p = 4$



Outlook:

- Integration of Limaçon-microlasers
- Deterministic fabrication technology (CL-lithography)
- Resonance tuning exploiting the QCSE
- On-chip resonance fluorescence experiments

